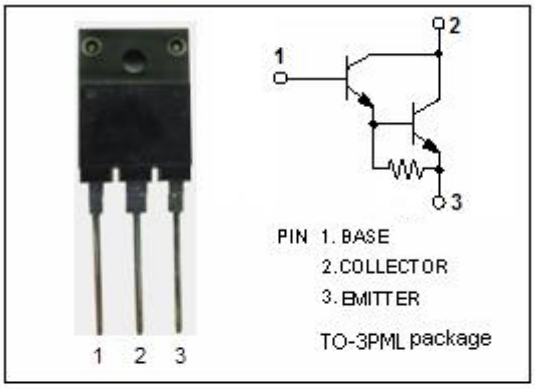
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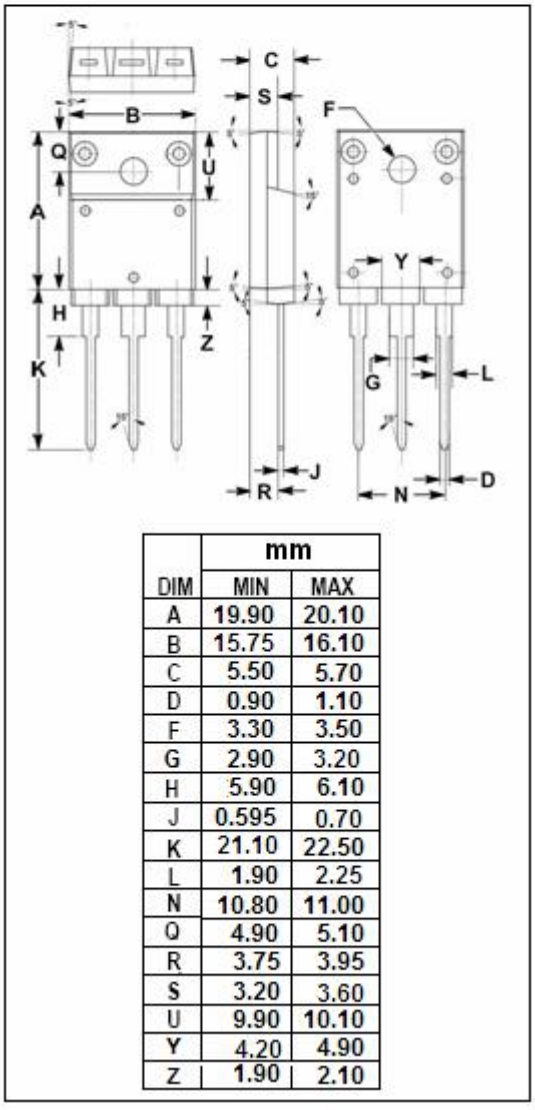


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 200V(Min)
- High DC current gain
  : h_{FE}= 1000(Min) @I_C= 1A
- Low Collector Saturation Voltgae-
  : $V_{CE(sat)}$= 1.5V(Max.)@ I_C= 1A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Audio ,regulator and general purpose



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ T_C=25℃	85	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=30mA ;I_B=0	200			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=10A ;I_B=10mA			2.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=10A ;I_B=10mA			3.0	V
I_{CBO}	Collector cut-off current	V_{CB}=200V I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=10A ; V_{CE}=4V	5000		30000	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		120		pF
f_T	Transition frequency	I_E=-2A ; V_{CE}=12V		70		MHz

◆ **h_{FE} Classifications**

O	P	Y
5000-12000	6500-20000	15000-30000